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Charge transport and trap states in lead sulfide quantum dot field-effect transistors

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**Charge Transport and Trap States in
Lead Sulfide Quantum Dot
Field-Effect Transistors**

Mohamad Insan Nugraha

Charge Transport and Trap States in Lead Sulfide Quantum Dot Field-Effect Transistors

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and in accordance with
the decision by the College of Deans

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